Application Information

NOISE FREE PROPERTIES

The noise current of the PIN diodes is negligible. This is a direct result of the exceptionally low leakage current, in accordance with the shot noise formula $I_N = (2qI_R\Delta f)^{1/2}$. Since the leakage current does not exceed 600 picoamps for the 5082-4204 at a reverse bias of 10 volts, shot noise current is less than 1.4×10^{-14} amp $Hz^{-1/2}$ at this voltage.

Excess noise is also very low, appearing only at frequencies below 10 Hz, and varying approximately as 1/f. When the output of the diode is observed in a load, thermal noise of the load resistance (R_L) is 1.28×10^{-10} $(R_L)^{-1/2} \times (\Delta f)^{1/2}$ at 25°C, and for exceeds the diode shot noise for load resistance less than 100 megohms (see Figure 6). Thus in high frequency operation where low values of load resistance are required for high cut-off frequency, all PIN photodiodes contribute virtually no noise to the system (see Figures 6 and 7).

HIGH SPEED PROPERTIES

Ultra-fast operation is possible because the HP PIN photodiodes are capable of a response time less than one nanosecond. A significant advantage of this device is that the speed of response is exhibited at relatively low reverse bias (−10 to −20 volts).

OFF-AXIS INCIDANCE RESPONSE

Response of the photodiodes to a uniform field of radiant incidance E_e, parallel to the polar axis is given by $I = (RA) \times E_e$ for 770nm. The response from a field not parallel to the axis can be found by multiplying (RA) by a normalizing factor obtained from the radiation pattern at the angle of operation. For example, the multiplying factor for the 5082-4207 with incidance E_e at an angle of 40° from the polar axis is 0.8. If $E_e = 1mW/cm^2$, then $I_p = k \times (RA) \times E_e$; $I_p = 0.8 \times 4.0 \times 1 = 3.2$ μamps.

SPECTRAL RESPONSE

To obtain the response at a wavelength other than 770nm, the relative spectral response must be considered. Referring to the spectral response curve, Figure 1, obtain response, X, at the wavelength desired. Then the ratio of the response at the desired wavelength to response at 770nm is given by:

$$\text{RATIO} = \frac{X}{0.5}$$

Multiplying this ratio by the incidance response at 770nm gives the incidance response at the desired wavelength.

ULTRAVIOLET RESPONSE

Under reverse bias, a region around the outside edge of the nominal active area becomes responsive. The width of this annular ring is approximately 25μm (0.001 inch) at −20V, and expands with higher reverse voltage. Responsivity in this edge region is higher than in the interior, particularly at shorter wavelengths; at 400nm the interior, responsivity is 0.1 A/W while edge responsivity is 0.35 A/W. At wavelengths shorter than 400nm, attenuation by the glass window affects response adversely. Speed of response for edge incidance is t_r, $t_f \approx 300ns$.

5082-4205 MOUNTING RECOMMENDATIONS

a. The 5082-4205 is intended to be soldered to a printed circuit board having a thickness of from 0.51 to 1.52mm (0.02 to 0.06 inch).
b. Soldering temperature should be controlled so that at no time does the case temperature approach 280° C. The lowest solder melting point in the device is 280° C (gold-tin eutectic). If this temperature is approached, the solder will soften, and the lens may fall off. Lead-tin solder is recommended for mounting the package, and should be applied with a small soldering iron, for the shortest possible time, to avoid the temperature approaching 280° C.
c. Contact to the lens end should be made by soldering to one or both of the tabs provided. Care should be exercised to prevent solder from coming in contact with the lens.
d. If printed circuit board mounting is not convenient, wire leads may be soldering or welded to the devices using the precautions noted above.

LINEAR OPERATION

Having an equivalent circuit as shown in Figure 9, operation of the photodiode is most linear when operated with a current amplifier as shown in Figure 10.

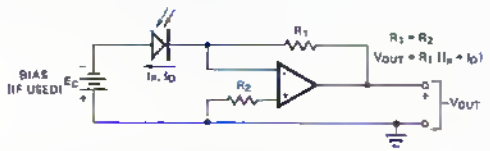

Figure 10. Linear Operation.

Lowest noise is obtained with $E_c = 0$, but higher speed and wider dynamic range are obtained if $5 < E_c < 20$ volts. The amplifier should have as high an input resistance as possible to permit high loop gain. If the photodiode is reversed, bias should also be reversed.

LOGARITHMIC OPERATION

If the photodiode is operated at zero bias with a very high impedance amplifier, the output voltage will be:

$$V_{OUT} = \left(1 + \frac{R_2}{R_1}\right) \cdot \frac{kT}{q} \cdot \ln \left(1 + \frac{I_P}{I_S}\right)$$

where $I_S = I_F \left(e^{\frac{qV}{kT}} - 1\right)^{-1}$ at $0 < I_F < 0.1mA$

using a circuit as shown in Figure 11.

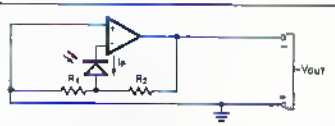

Figure 11. Logarithmic Operation.

Output voltage, V_{OUT}, is positive as the photocurrent, I_P, flows back through the photodiode making the anode positive.